

Silicon NPN Power Transistors

2SC2927

DESCRIPTION

- With TO-220 package
- High collector-emitter voltage
: $V_{CEO}=300V$
- High frequency: $f_T=40MHz$ (Min)

APPLICATIONS

- For use in line-operated color TV chroma output circuits and sound output circuits.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

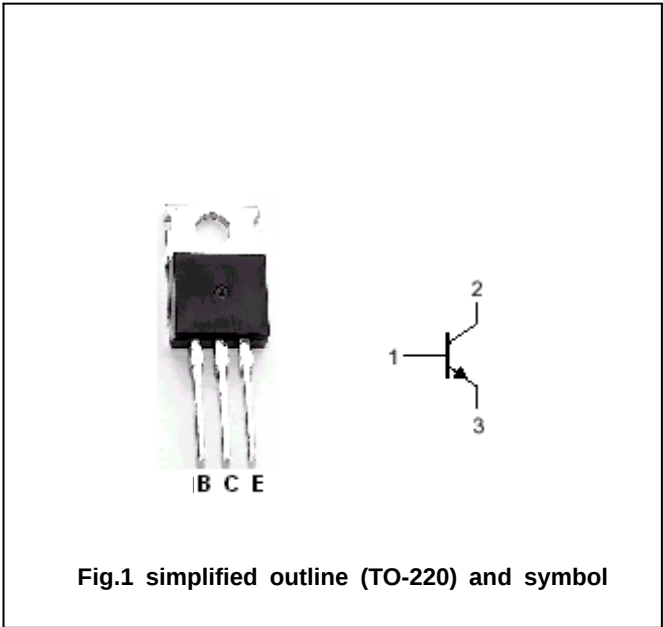


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		0.2	A
P_T	Collector power dissipation	$T_C=25^{\circ}C$	10	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=10\ \mu\text{A}$; $I_E=0$	300			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=1\text{mA}$; $I_B=0$	300			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=10\ \mu\text{A}$; $I_C=0$	7			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=50\text{mA}$; $I_B=5\text{mA}$			2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=200\text{V}$; $I_E=0$			0.1	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5\text{V}$; $I_C=0$			0.1	μA
h_{FE}	DC current gain	$I_C=10\text{mA}$; $V_{CE}=10\text{V}$	40		200	
f_T	Transition frequency	$I_C=10\text{mA}$; $V_{CE}=30\text{V}$	40	80		MHz

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PACKAGE OUTLINE

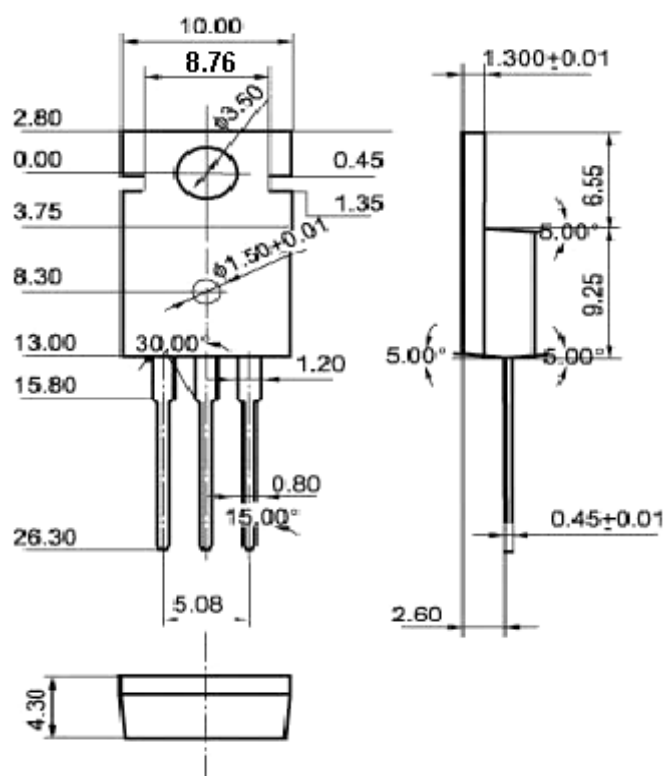


Fig.2 outline dimensions (unindicated tolerance: ±0.10 mm)